60 V, single N-channel Trench MOSFET

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	200	mA
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 100 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_j = 25 °C		-	2.7	4.5	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source	3	
3	D	drain	1 2 SOT23	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BSS138AKA		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
BSS138AKA	%JL

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	200	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	125	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	800	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	300	mW
			[1]	-	360	mW
		T _{sp} = 25 °C		-	1060	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode			'		
Is	source current	T _{amb} = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

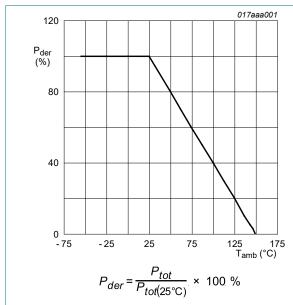


Fig. 1. Normalized total power dissipation as a function of ambient temperature

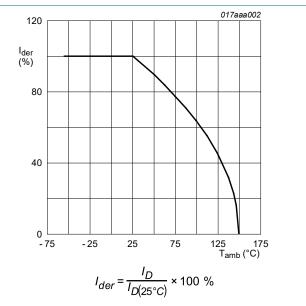


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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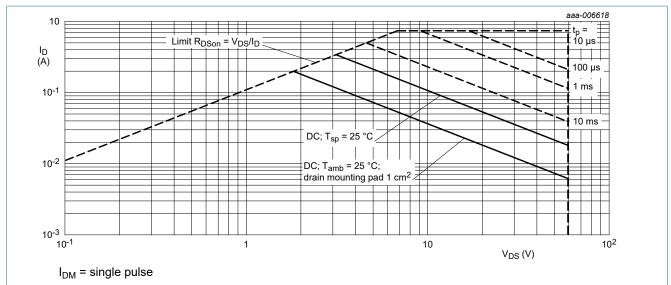


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

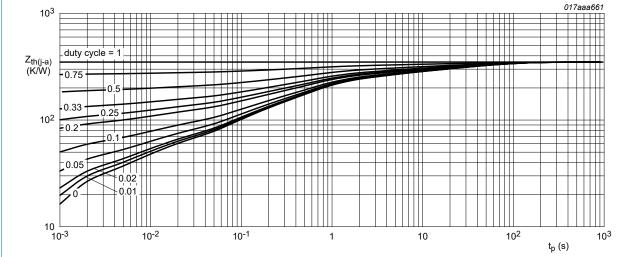
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9. Thermal characteristics

Table 6. Thermal characteristics

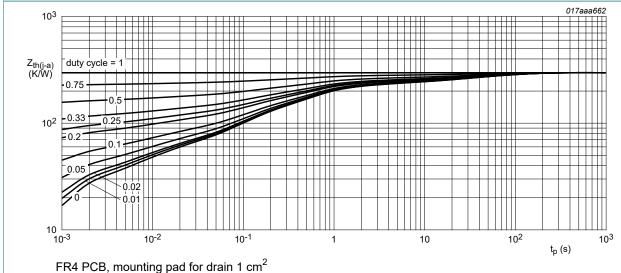
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	350	400	K/W
junction to ambient	junction to ambient		[2]	-	300	340	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



1114 1 Ob, modifiing pad for drain 1 on

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.8	1.2	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-3.5	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μΑ
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-0.5	μΑ
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 100 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_j = 25 °C	-	2.7	4.5	Ω
		V_{GS} = 10 V; I_{D} = 100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{j} = 150 °C	-	5.5	9.2	Ω
		V_{GS} = 4.5 V; I_{D} = 100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{j} = 25 °C	-	3	5.2	Ω
		V_{GS} = 2.5 V; I_{D} = 10 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{j} = 25 °C	-	4	13	Ω
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 150 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{j} = 25 °C	320	-	-	mS
Dynamic ch	naracteristics	-				
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 150 mA; V _{GS} = 4.5 V;	-	0.39	0.51	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	13	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.6	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 40 V; R _L = 250 Ω; V _{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
$t_{d(off)}$	turn-off delay time		-	36	72	ns
t _f	fall time		-	22	-	ns
Source-drai	in diode		1			
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.7	1.2	V

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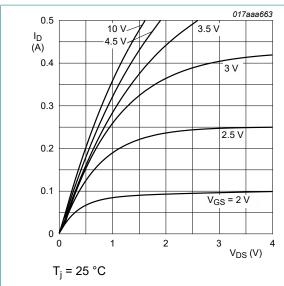


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

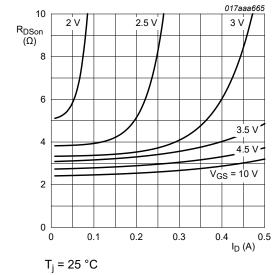


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

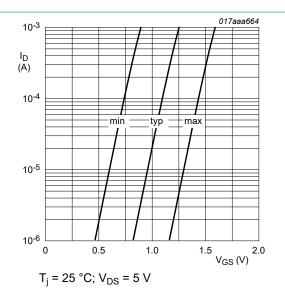


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

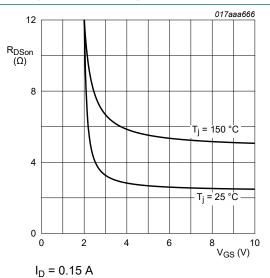


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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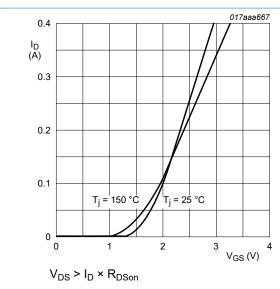


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

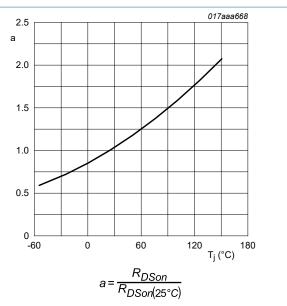


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

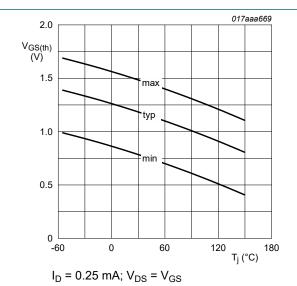


Fig. 12. Gate-source threshold voltage as a function of junction temperature

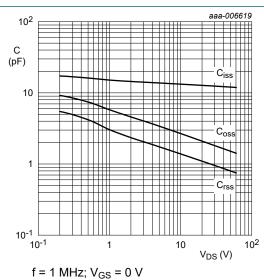


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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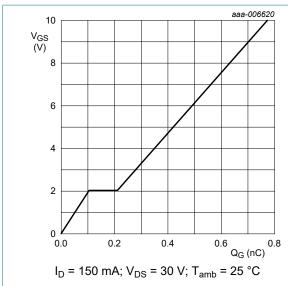


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

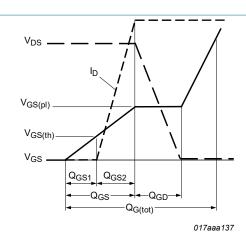


Fig. 15. Gate charge waveform definitions

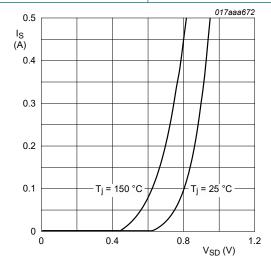
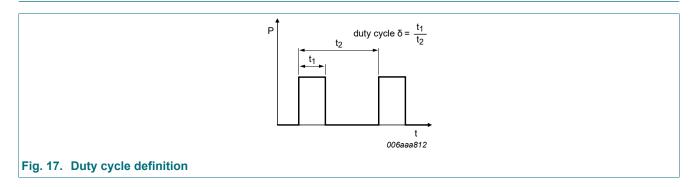


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

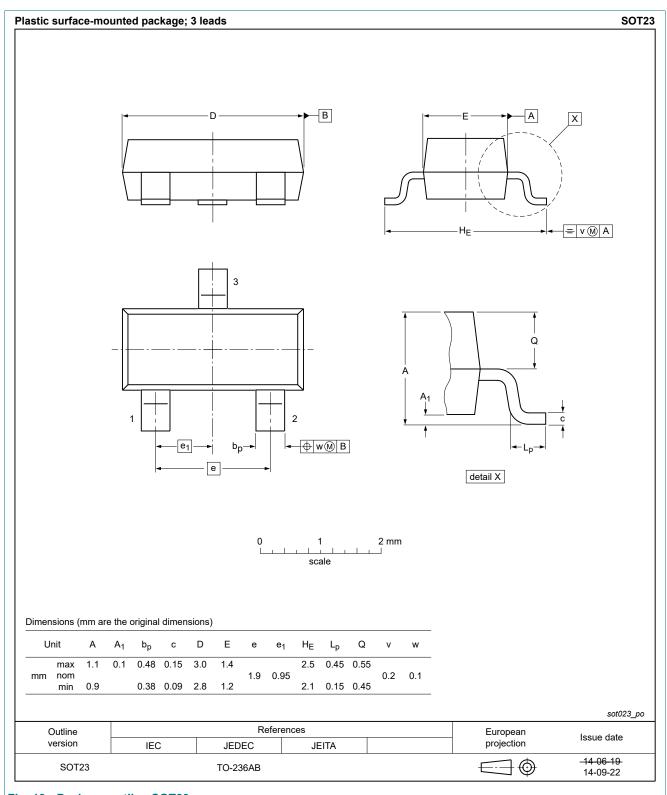
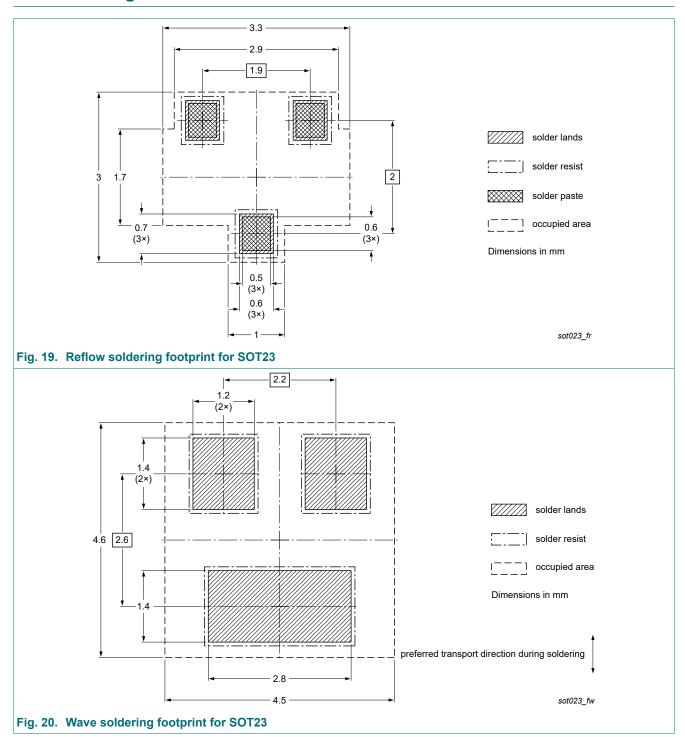


Fig. 18. Package outline SOT23

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13. Soldering



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14. Revision history

Table 8. Revision history

Table of Revision metery							
Release date	Data sheet status	Change notice	Supersedes				
20240202	Product data sheet	-	BSS138AKA v.3				
Chapter "Characteris	Chapter "Characteristics": typo correction for the V _{GSth} condition						
20150429	Product data sheet	-	BSS138AKA v.3				
20141103	Product data sheet	-	BSS138AKA v.2				
20130206	Product data sheet	-	-				
	Release date 20240202 • Chapter "Characteris 20150429 20141103	Release date 20240202 Product data sheet Chapter "Characteristics": typo correction for the content of the c	Release date Data sheet status Change notice 20240202 Product data sheet - • Chapter "Characteristics": typo correction for the V _{GSth} condition 20150429 Product data sheet - 20141103 Product data sheet -				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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